

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

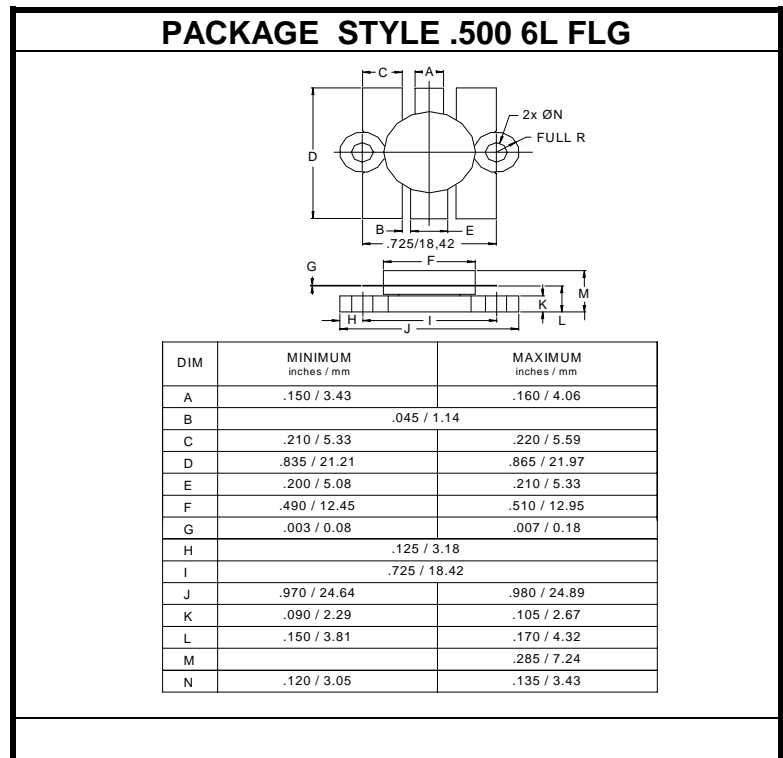
The **ASI MRF650** is Designed for Class C, FM Land Mobile Applications up to 470 MHz.

FEATURES:

- Internal Input Matching Network
- $P_G = 5.0$ dB at 45 W/470 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	12 A
V_{CBO}	36 V
V_{CEO}	16 V
V_{CES}	36 V
V_{EBO}	4.0 V
P_{DISS}	175 W @ $T_C = 25^\circ\text{C}$
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	1.0 °C/W


CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 50$ mA	16			V
BV_{CES}	$I_C = 20$ mA	36			V
BV_{CBO}	$I_C = 5.0$ mA	36			
BV_{EBO}	$I_E = 5.0$ mA	4.0			V
I_{CBO}	$V_{CB} = 15$ V			5.0	mA
I_{CES}	$V_{CE} = 22$ V			5.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 5.0$ A	20		200	---
C_{ob}	$V_{CB} = 12.5$ V $f = 1.0$ MHz			150	pF
P_G η_C	$V_{CE} = 12.5$ V $P_{OUT} = 45$ W $f = 470$ MHz	5.0	60		dB %